VITELIC

V53C256A FAMILY
HIGH PERFORMANCE, LOW POWER
256K X 1 BIT FAST PAGE MODE
CMOS DYNAMIC RAM

HIGH PERFORMANCE V53C256A	60/60L	70/70L	80/80L	10/10L
Max. $\overline{RAS}$ Access Time, (t_{RAC})	60 ns	70 ns	80 ns	100 ns
Max. Column Address Access Time, (t_{CAA})	30 ns	35 ns	40 ns	45 ns
Max. $\overline{CAS}$ Access Time, (t_{CAC})	15 ns	15 ns	20 ns	25 ns
Min. Fast Page Mode Cycle Time, (t_{PC})	45 ns	50 ns	55 ns	60 ns
Min. Read-Write Cycle Time, (t_{RC})	115 ns	130 ns	145 ns	175 ns

LOW POWER V53C256AL	60L	70L	80L	10L
Max. CMOS Standby Current, (I_{DD6})	1.2 mA	1.2 mA	1.2 mA	1.2 mA

2

Features

- Low power dissipation for V53C256A-10
  - Operating Current—60 mA max.
  - TTL Standby Current—3.5 mA max.
- Low CMOS Standby Current
  - V53C256A—3.0 mA max.
  - V53C256AL—1.2 mA max.
- Read-Modify-Write, $\overline{RAS}$-Only Refresh, $\overline{CAS}$-before-$\overline{RAS}$ Refresh capability
- Common I/O capability
- Fast Page Mode operation for a sustained data rate greater than 21 MHz.
- 256 Refresh cycles/4 ms
- Standard packages are 16 pin Plastic DIP and 18 pin PLCC

Description

The Vitelic V53C256A is a high speed 262,144 x 1 bit CMOS dynamic random access memory. Fabricated with Vitelic's VICMOS III technology, the V53C256A offers a combination of size and features unattainable with NMOS technology: Fast Page Mode for high data bandwidth, fast usable speed, CMOS standby current and, for the V53C256AL, reduced CMOS standby mode supply current (I_{DD6}).

All inputs and outputs are TTL compatible. Input and output capacitances are significantly lowered to allow increased system performance. Fast Page Mode operation allows random or sequential access of up to 512 bits within a row with cycle times as short as 50 ns. Because of static circuitry, the $\overline{CAS}$ clock is not in the critical timing path. The flow-through column address latches allow address pipelining while relaxing many critical timing requirements for fast usable speed. These features make the V53C256 ideally suited for cache based mainframe and mini computers, graphics, digital signal processing and high performance microprocessor systems.

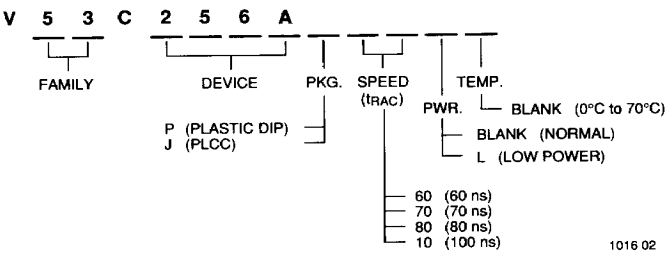
The V53C256AL-10 offers a maximum data retention power of 10 mW when operating in CMOS standby mode and performing $\overline{RAS}$-only or $\overline{CAS}$-before-$\overline{RAS}$ refresh cycles. This mode is entered by holding RAS at a voltage greater than V_{DD}–0.2 when it is inactive.

Device Usage Chart

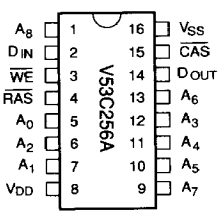
Operating Temperature Range	Package Outline		Access Time (ns)				Power		Temperature Mark
	P	J	60	70	80	100	Low	Std.	
0°C to 70°C	•	•	•	•	•	•	•	•	Blank

V53C256A Rev.00 June 1990

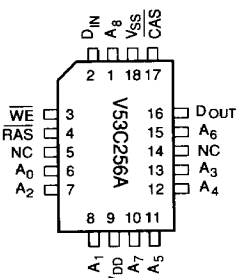
Package	Pkg.	Pin Count
Plastic DIP	P	16
PLCC	J	18



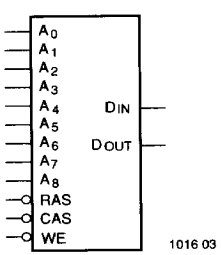
16 Lead Plastic DIP PIN CONFIGURATION
Top View



18 Lead PLCC Package PIN CONFIGURATION
Top View



LOGIC SYMBOL



Absolute Maximum Ratings*

Ambient Temperature
Under Bias ..... −10°C to +80°C
Storage Temperature (plastic) .... −55°C to +125°C
Voltage on any Pin Except V_{DD}
Relative to V_{SS} ..... −1.0 V to +7.0 V
Voltage on V_{DD} relative to V_{SS} ..... −1.0 V to +7.0 V
Data Out Current ..... 50 mA
Power Dissipation ..... 1.0 W

*Note: Operation above Absolute Maximum Ratings can adversely affect device reliability.

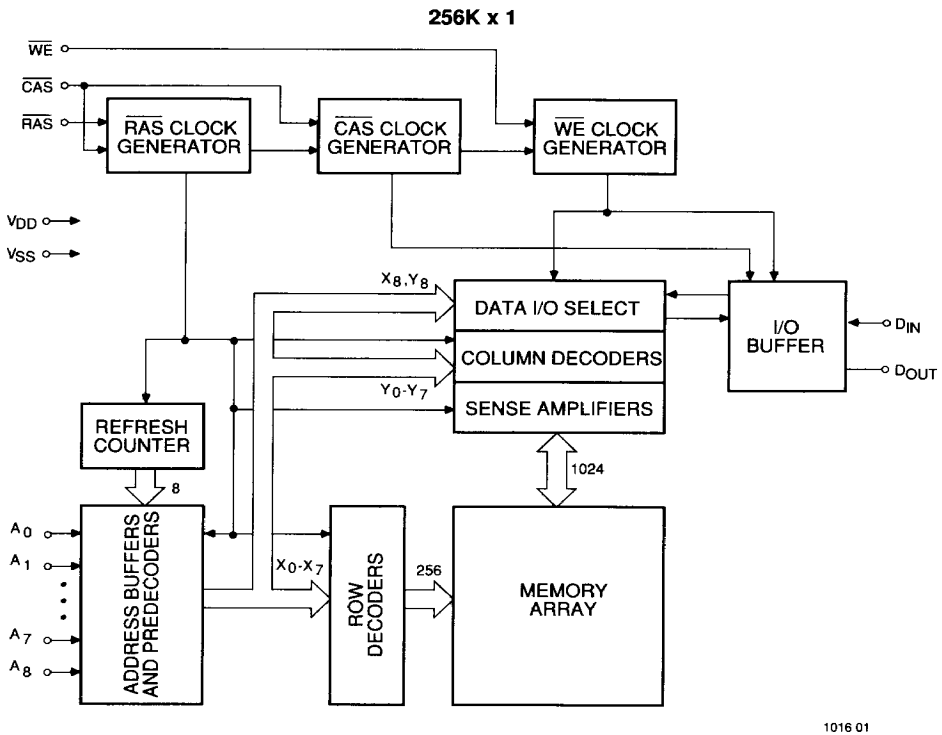
Capacitance*

T_A = 25°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V

Symbol	Parameter	Typ.	Max.	Unit
C_{IN1}	Address, D_{IN}	3	4	pF
C_{IN2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	4	5	pF
C_{OUT}	D_{OUT}	4	6	pF

*Note: Capacitance is sampled and not 100% tested

Block Diagram



DC and Operating Characteristics

T_A = 0°C to 70°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V, unless otherwise specified.

Symbol	Parameter	Access Time	V53C256A		V53C256AL		Unit	Test Conditions	Notes
			Min.	Max.	Min.	Max.			
I_{LI}	Input Leakage Current (any input pin)		−10	10	−10	10	µA	$V_{SS} \le V_{IN} \le V_{DD}$	
I_{LO}	Output Leakage Current (for High-Z State)		−10	10	−10	10	µA	$V_{SS} \le D_{OUT} \le V_{DD}$ $\overline{RAS}$,$\overline{CAS}$ at V_{IH}	
I_{DD1}	V_{DD} Supply Current, Operating	60		80		80	mA	$t_{RC} = t_{RC}$ (min.)	1,2
		70		70		70			
		80		65		65			
		100		60		60			
I_{DD2}	V_{DD} Supply Current, TTL Standby			3.5		2.0	mA	$\overline{RAS}$,$\overline{CAS}$ at V_{IH} other inputs ≥ V_{SS}	
I_{DD3}	V_{DD} Supply Current, $\overline{RAS}$-Only Refresh	60		80		80	mA	$t_{RC} = t_{RC}$ (min.)	2
		70		70		70			
		80		60		60			
		100		50		50			
I_{DD4}	V_{DD} Supply Current, Fast Page Mode Operation	60		50		50	mA	Minimum Cycle	1,2
		70		45		45			
		80		40		40			
		100		35		35			
I_{DD5}	V_{DD} Supply Current, Standby, Output Enabled			4		2.5	mA	$\overline{RAS}$=V_{IH},$\overline{CAS}$=V_{IL} other inputs ≥ V_{SS}	1
I_{DD6}	V_{DD} Supply Current, CMOS Standby			3		1.2	mA	$\overline{RAS} \ge V_{DD}$ −0.2 V, $\overline{CAS}$ = V_{IH}, other inputs ≥ V_{SS}	
V_{IL}	Input Low Voltage (all inputs)		−1	0.8	−1	0.8	V		3
V_{IH}	Input High Voltage (all inputs)		2.4	V_{DD} +1	2.4	V_{DD} +1	V		3
V_{OL}	Output Low Voltage			0.4		0.4	V	I_{OL} = 4.2 mA	
V_{OH}	Output High Voltage		2.4		2.4		V	I_{OH} = −5 mA	

AC Characteristics

T_A = 0°C to 70°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V, unless otherwise noted

#	JEDEC Symbol	Symbol	Parameter	60/60L		70/70L		80/80L		10/10L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
1	t_{RL1RH1}	t_{RAS}	$\overline{RAS}$ Pulse Width	60	75K	70	75K	80	75K	100	75K	ns	
2	t_{RL2RL2}	t_{RC}	Read or Write Cycle Time	115		130		145		175		ns	
3	t_{RH2RL2}	t_{RP}	$\overline{RAS}$ Precharge Time	45		50		55		65		ns	
4	t_{AVRL2}	t_{ASR}	Row Address Setup Time	0		0		0		0		ns	
5	t_{RL1AX}	t_{RAH}	Row Address Hold Time	10		15		15		15		ns	
6	t_{AVRH1}	t_{CAR}	Column Address to $\overline{RAS}$ Setup Time	30		35		40		45		ns	
7	t_{RL1AV}	t_{RAD}	$\overline{RAS}$ to Column Address Delay Time	15	30	20	35	20	40	20	55	ns	4
8	t_{AVCL2}	t_{ASC}	Column Address Setup Time	0		0		0		0		ns	
9	t_{CL1AX}	t_{CAH}	Column Address Hold Time	10		15		15		20		ns	
10	t_{RL1CL1}	t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay	20	45	25	55	25	60	25	75	ns	5
11	t_{RL1QV}	t_{RAC}	Access Time from $\overline{RAS}$		60		70		80		100	ns	6,7,8
12	t_{AVQV}	t_{CAA}	Access Time from Column Address		30		35		40		45 15	ns	8,9,
13	t_{CL1QV}	t_{CAC}	Access Time from $\overline{CAS}$		15		15		20		25	ns	8,15
14	$t_{CL1CH1(R)}$	$t_{CAS(R)}$	$\overline{CAS}$ Pulse Width in Read Cycle	15	75K	15	75K	20	75K	25	75K	ns	
15	$t_{CL1RH1(R)}$	$t_{RSH(R)}$	$\overline{RAS}$ Hold Time (Read Cycle)	15		15		20		25		ns	
16	t_{WH2CL2}	t_{RCS}	Read Command Setup Time	0		0		0		0		ns	
17	t_{CH2WX}	t_{RCH}	Read Command Hold Time Referenced to $\overline{CAS}$	0		5		5		5		ns	10
18	t_{RH2WX}	t_{RRH}	Read Command Hold Time Referenced to $\overline{RAS}$	5		5		5		5		ns	10
19	t_{CH2RL2}	t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	10		15		15		15		ns	
20	t_{CH2QX}	t_{OFF}	Output Buffer Turn Off Delay	0	15	0	15	0	20	0	25	ns	11

AC Characteristics (Cont'd.)

#	JEDEC Symbol	Symbol	Parameter	60/60L		70/70L		80/80L		10/10L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
21	t_{CH2QV}	t_{OH}	Data Hold Time from $\overline{CAS}$	0		0		0		0		ns	11
22	t_{WL1WH1}	t_{WP}	Write Pulse Width	10		15		15		20		ns	
23	t_{CH2CL2}	t_{CP}	$\overline{CAS}$ Precharge Time	10		15		15		20		ns	
24	t_{RL1AX}	t_{AR}	Column Address Hold Time from $\overline{RAS}$	50		55		60		70		ns	
25	$t_{CL1CH1(W)}$	$t_{CAS(W)}$	$\overline{CAS}$ Pulse Width in Write Cycle	20		20		25		30		ns	
26	$t_{CL1RH1(W)}$	$t_{RSH(W)}$	$\overline{RAS}$ or $\overline{CAS}$ Hold Time in Write Cycle	20		25		25		30		ns	
27	t_{RL1WH1}	t_{WCR}	Write Command Hold Time from $\overline{RAS}$	50		55		60		70		ns	
28	t_{WL1CL2}	t_{WCS}	Write Command Setup Time	0		0		0		0		ns	12,13
29	t_{CL1WH1}	t_{WCH}	Write Command Hold Time	10		15		15		20		ns	
30	t_{DVWL2}	t_{DS}	Data In Setup Time	0		0		0		0		ns	14
31	t_{WH1DX}	t_{DH}	Data In Hold Time	15		15		15		20		ns	14
32	t_{RL1DX}	t_{DHR}	Data In Hold Time Referenced to $\overline{RAS}$	50		55		60		70		ns	
33	t_{RL2RL2} (RMW)	t_{RWC}	Read-Modify-Write Cycle Time	140		155		175		210		ns	
34	t_{RL1RH1} (RMW)	t_{RRW}	Read-Modify-Write Cycle $\overline{RAS}$ Pulse Width	85		95		110		135		ns	
35	t_{RL1WL2}	t_{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay In Read-Modify-Write Cycle	60		70		80		100		ns	12
36	t_{CL1WL2}	t_{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay	15		15		20		25		ns	12
37	t_{AVWL2}	t_{AWD}	Column Address to $\overline{WE}$ Delay	30		35		40		45		ns	12
38	t_{CH2QV}	t_{CAP}	Access Time from Column Precharge		40		45		50		55	ns	15
39	$t_{CL2CL2(R)}$	t_{PC}	Fast Page Mode Read or Write Cycle Time	45		50		55		60		ns	

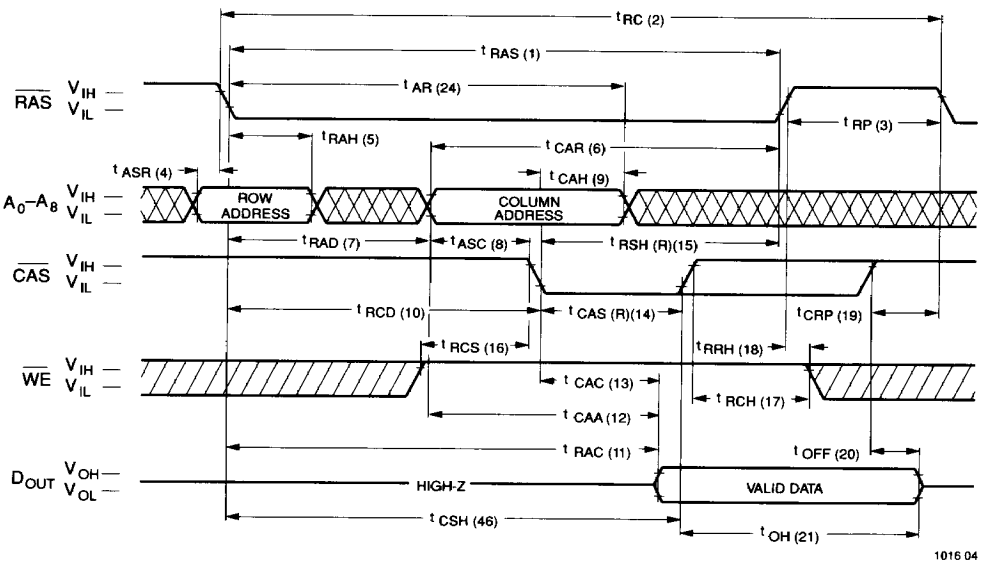
AC Characteristics (Cont'd.)

#	JEDEC Symbol	Symbol	Parameter	60/60L		70/70L		80/80L		10/10L		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
40	t_{CL2CL2} (RMW)	t_{PCM}	Fast Page Mode Read-Modify-Write Cycle Time	70		75		85		95		ns	
41	t_{WL1RH1}	t_{RWL}	Write Command to $\overline{RAS}$ Lead Time	20		20		25		30		ns	
42	t_{WL1CH1}	t_{CWL}	Write Command to $\overline{CAS}$ Lead Time	20		20		25		30		ns	
43	t_{RH2CL2}	t_{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	0		0		0		0		ns	
44	t_{CL1RL2}	t_{CSR}	$\overline{CAS}$ Setup Time $\overline{CAS}$-before-$\overline{RAS}$ Refresh	10		10		10		10		ns	
45	t_{RL1CH1}	t_{CHR}	$\overline{CAS}$ Hold Time $\overline{CAS}$-before-$\overline{RAS}$ Cycle	15		20		25		30		ns	
46	t_{RL1CH1}	t_{CSH}	$\overline{CAS}$ Hold Time	60		70		80		100		ns	
47	t_T	t_T	Transition Time (Rise and Fall)	3	25	3	25	3	25	3	25	ns	16
		t_{RI}	Refresh Interval (256 Cycles)	4			4		4		4	ms	17

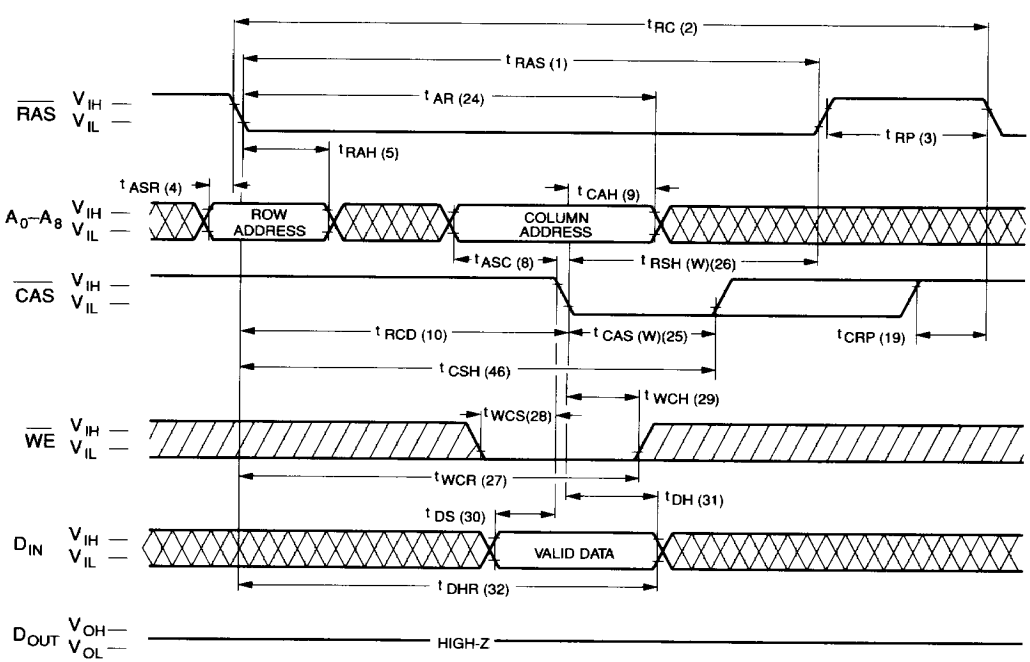
Notes:

1. I_{DD} is dependent on output loading when the device output is selected. Specified I_{DD} (max.) is measured with the output open.
2. I_{DD} is dependent upon the number of address transitions. Specified I_{DD} (max.) is measured with a maximum of two transitions per address cycle in Fast Page Mode.
3. Specified V_{IL} (min.) is steady state operation. During transitions, V_{IL} (min.) may undershoot to −1.0 V for periods not to exceed 20 ns. All AC parameters are measured with V_{IL} (min.) ≥ V_{SS} and V_{IH} (max.) ≤ V_{DD}.
4. Operation within the t_{RAD} (max.) limit ensures that t_{RAC} (max.) can be met. t_{RAD} (max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (max.) limit, the access time is controlled by t_{CAA} and t_{CAC}.
5. t_{RCD} (max.) is specified for reference only. Operation within t_{RCD} (max.) and t_{RAD} (max.) limits ensure that t_{RAC} (max.) and t_{CAA} (max.) can be met. If t_{RCD} is greater than the specified t_{RCD} (max.), the access time is controlled by t_{CAA} and t_{CAC}.
6. Assumes that $t_{RAD} \leq t_{RAD}$ (max.). If t_{RAD} is greater than t_{RAD} (max.), t_{RAC} will increase by the amount that t_{RAD} exceeds t_{RAD} (max.).
7. Assumes that $t_{RCD} \leq t_{RCD}$ (max.). If t_{RCD} is greater than t_{RCD} (max.), t_{RAC} will increase by the amount that t_{RCD} exceeds t_{RCD} (max.).
8. Measured with a load equivalent to two TTL inputs and 100 pF in parallel.
9. Assumes that $t_{RAD} \geq t_{RAD}$ (max.).
10. Either t_{RRH} or t_{RCH} must be satisfied for a Read Cycle to occur.
11. t_{OFF} and t_{ON} define the time at which D_{OUT} reaches an open circuit condition and are not referenced to the output voltage levels.
12. t_{WCS}, t_{RWD}, t_{AWD} and t_{CWD} are not restrictive operating parameters.
13. t_{WCS} (min.) must be satisfied in an Early Write Cycle.
14. t_{DS} and t_{DH} are referenced to the later occurance of $\overline{CAS}$ or $\overline{WE}$.
15. Access time is determined by the longer of t_{CAA}, t_{CAC}, or t_{CAP}.
16. t_T is measured between V_{IH} (min.) and V_{IL} (max.). AC measurements assume t_T = 5 ns.
17. An initial 200 µs pause and 8 $\overline{RAS}$-containing cycles are required when exiting an extended period of bias without clocks. An extended period of time without clocks is defined as one that exceeds the specified Refresh Interval.

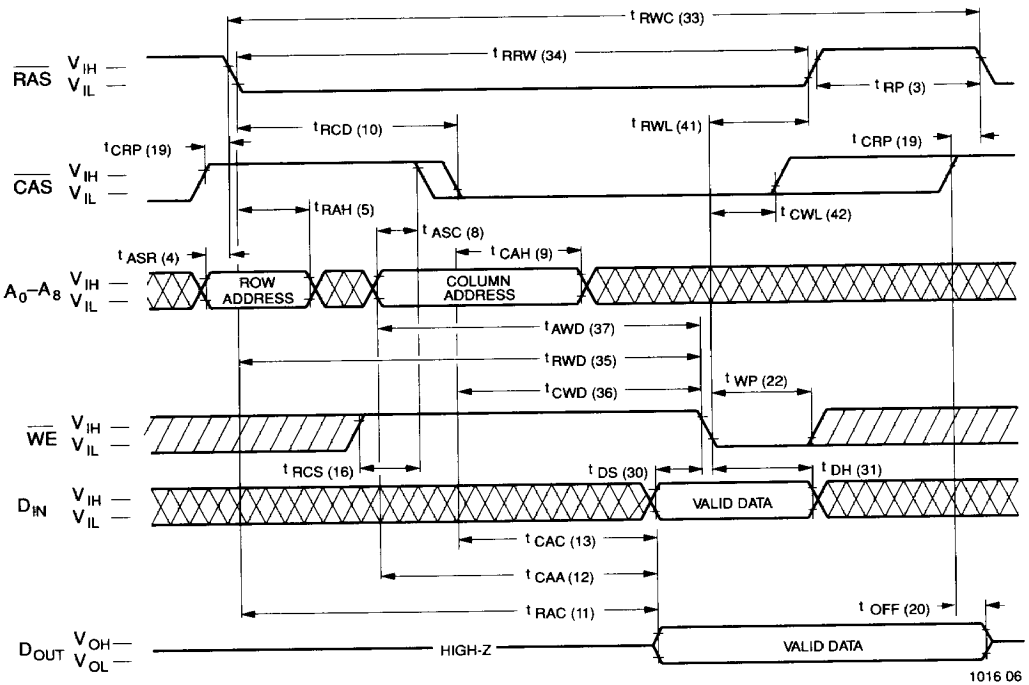
Waveforms of Read Cycle



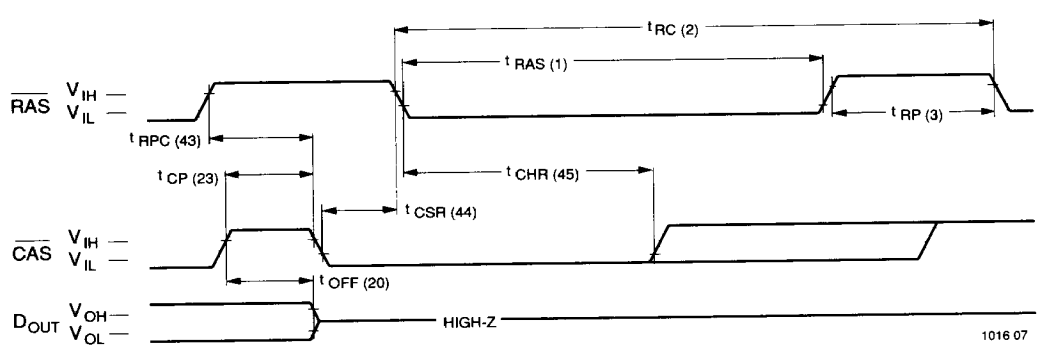
Waveforms of Early Write Cycle



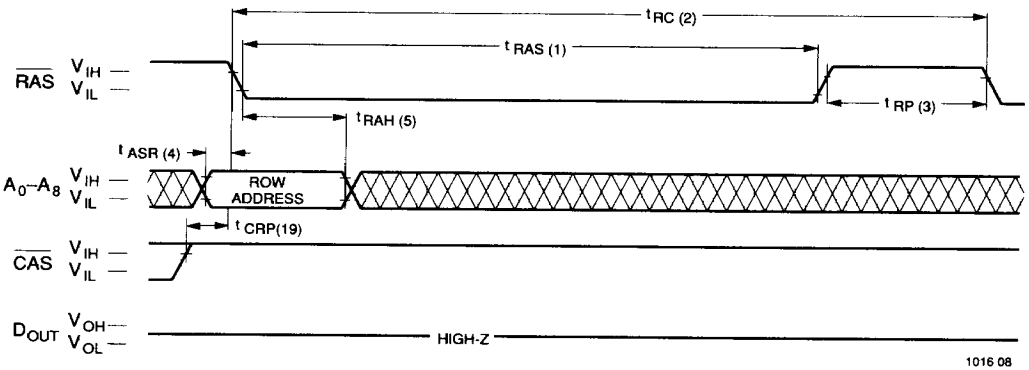
Waveforms of Read-Modify-Write Cycle



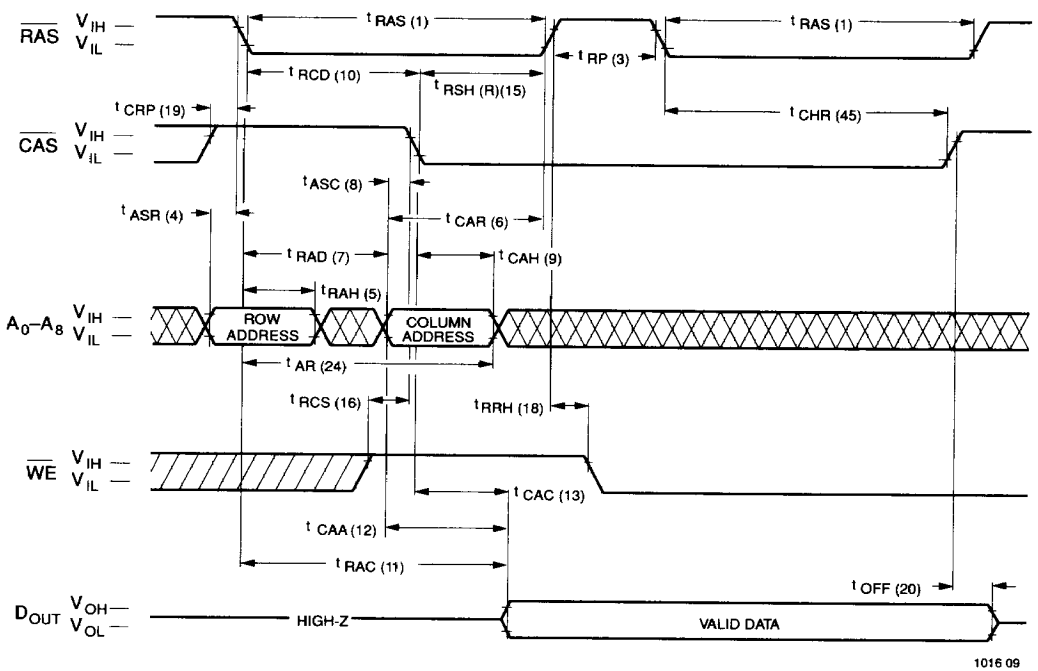
Waveforms of $\overline{RAS}$-Only Refresh Cycle



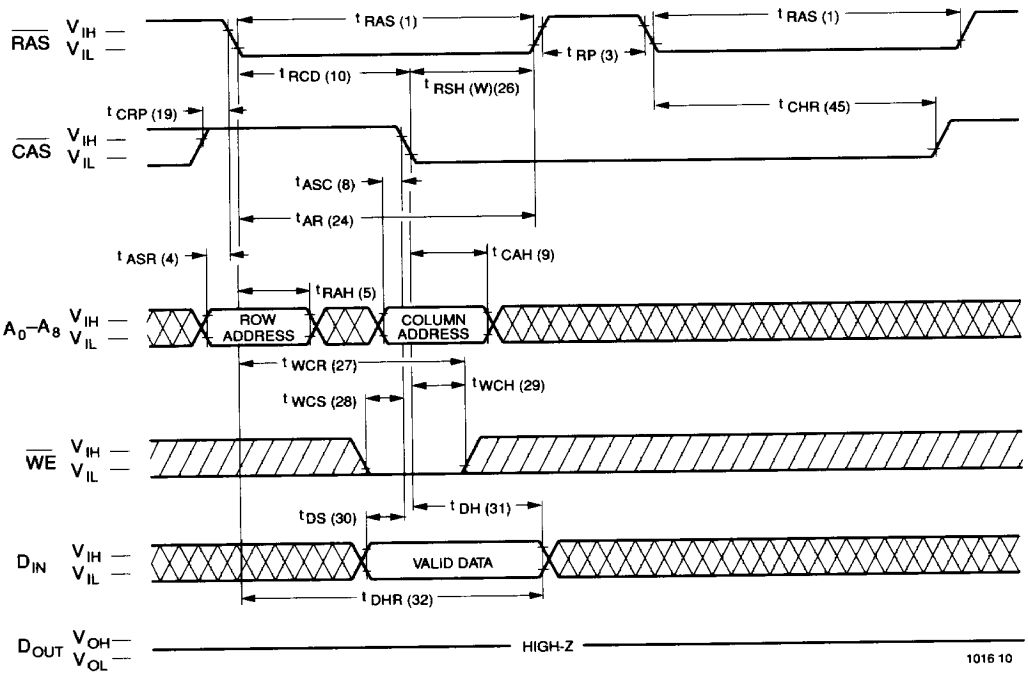
Waveforms of $\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle



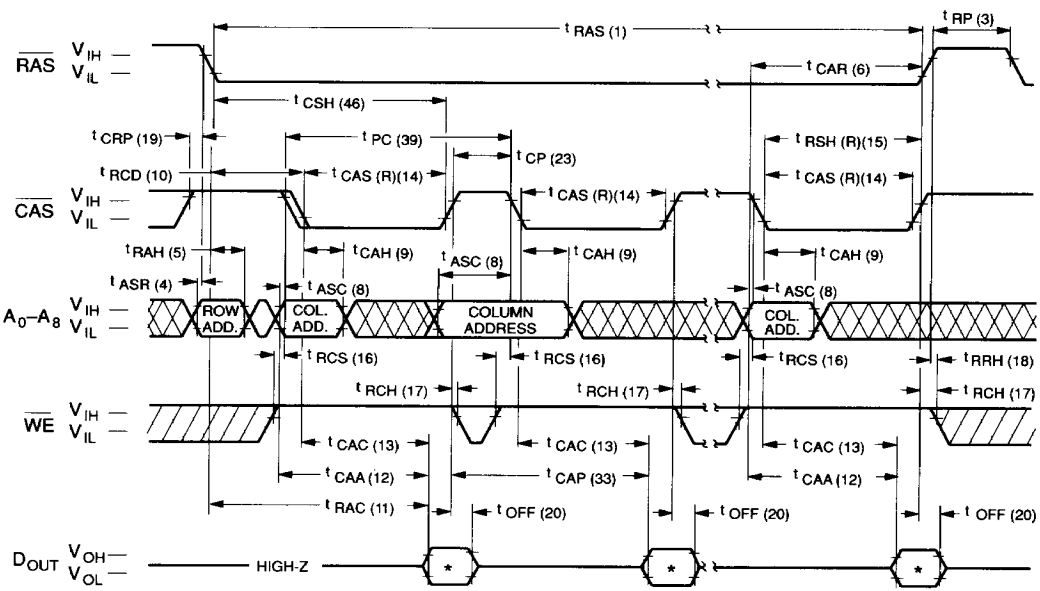
Waveforms of Hidden Refresh Cycle (Read)



Waveforms of Hidden Refresh Cycle (Write)

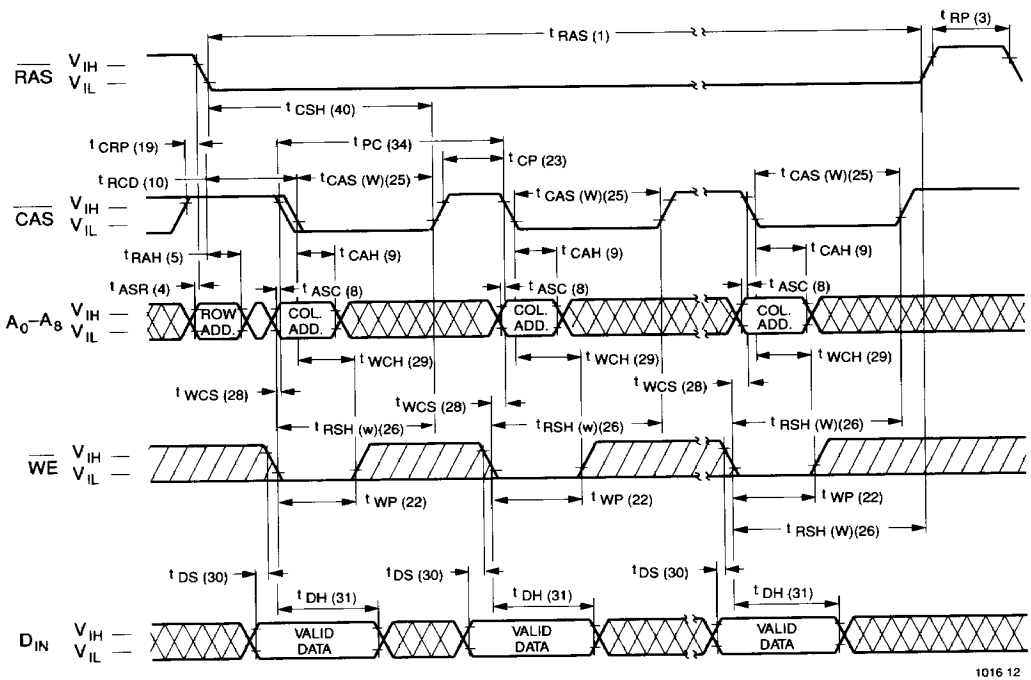


Waveforms of Fast Page Mode Read Cycle

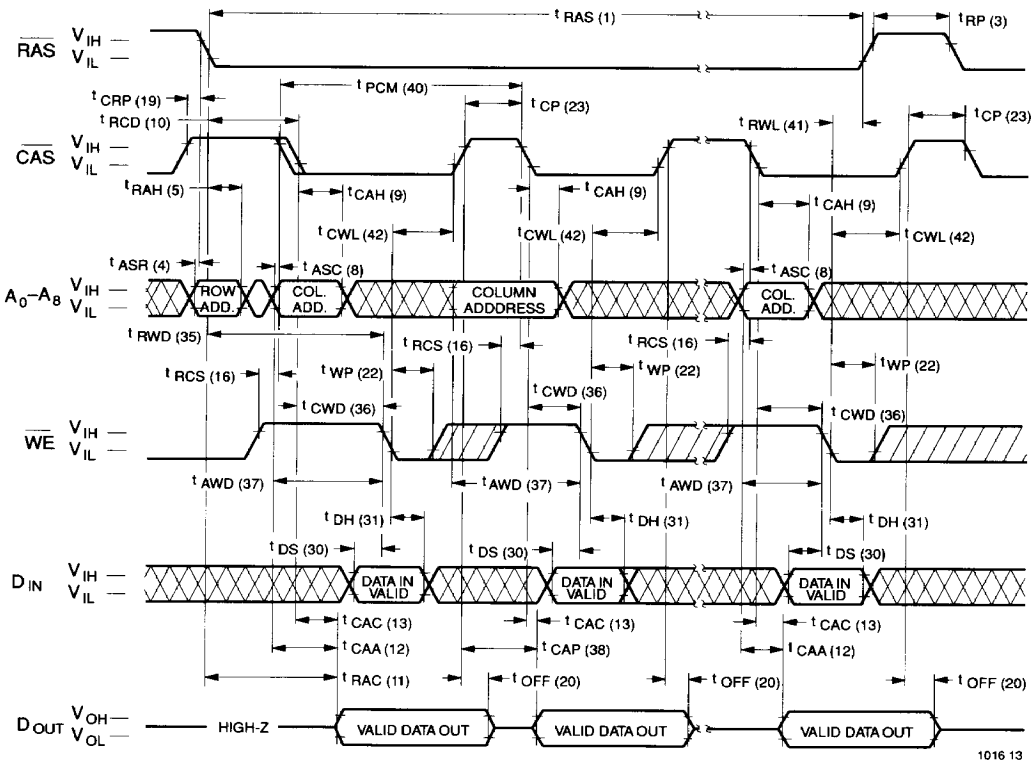


* Valid Data

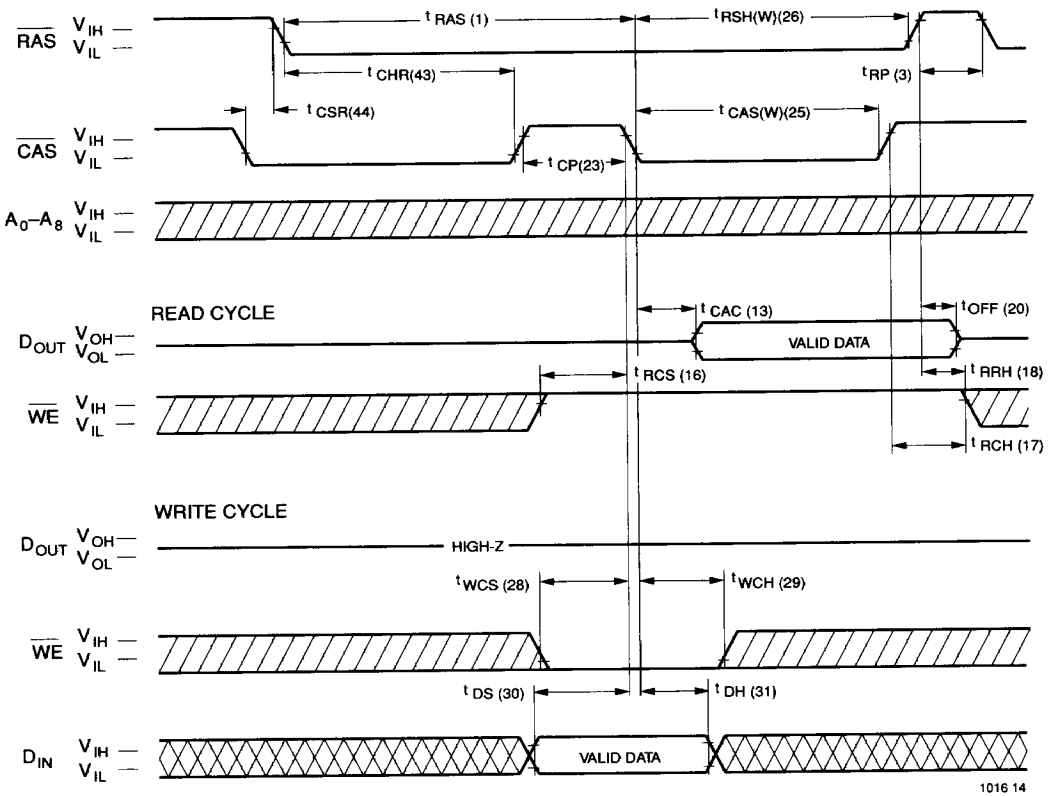
Waveforms of Fast Page Mode Write Cycle



Waveforms of Fast Page Mode Read-Modify-Write Cycle



Waveforms of Refresh Counter Test Cycle



Functional Description

The V53C256A is a CMOS dynamic RAM optimized for high data bandwidth, low power applications. It is functionally similar to a traditional dynamic RAM. The V53C256A reads and writes data by multiplexing an 18-bit address into a 9-bit row and a 9-bit column address. The row address is latched by the Row Address Strobe ($\overline{RAS}$). The column address flows through an internal address buffer and is latched by the Column Address Strobe ($\overline{CAS}$). Because access time is primarily dependent on a valid column address rather than the presice time that the $\overline{CAS}$ edge occurs, the delay from $\overline{RAS}$ to $\overline{CAS}$ has little effect on the access time.

Memory Cycle

A memory cycle is initiated by bringing $\overline{RAS}$ low. Any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. This ensures proper device operation and data integrity. A new cycle must not be initiated until the minimum precharge time t_{RP}/t_{CP} has elapsed.

Read Cycle

A read cycle is performed by holding the Write Enable ($\overline{WE}$) signal high during a $\overline{RAS}/\overline{CAS}$ operation. The column address must be held for a minimum time specified by t_{AR}. Data Out becomes valid only when t_{RAC}, t_{CAA} and t_{CAC} are all satisfied. As a result, the access time is dependent on the timing relationships between t_{RAC}, t_{CAA} and t_{CAC}. For example, the access time is limited by t_{CAA} when t_{RAC} (min.) and t_{CAC} (min.) are both satisfied.

Write Cycle

A write cycle is performed by taking $\overline{WE}$ and $\overline{CAS}$ low during a $\overline{RAS}$ operation. The column address is latched by $\overline{CAS}$. The write can be $\overline{WE}$ controlled or $\overline{CAS}$ controlled depending on whether $\overline{WE}$ or $\overline{CAS}$ falls later. Consequently, the input data must be valid at or before the falling edge of $\overline{WE}$ or $\overline{CAS}$, whichever occurs last. In the $\overline{CAS}$-controlled write cycle when the leading edge of $\overline{WE}$ occurs prior to the $\overline{CAS}$ low transition, the output (D_{OUT}) pin will be in the High-Z state at the beginning of the Write function. Ending the write with $\overline{RAS}$ or $\overline{CAS}$ will maintain the output in the High-Z state.

Refresh Cycle

To retain data, 256 refresh cycles are required in each 4 ms period. There are two ways to refresh the memory:

1. By clocking each of the 512 row addresses (A_0 through A_7) with $\overline{RAS}$ at least once every 4 ms. Any Read, Write, Read-Modify-Write or $\overline{RAS}$-only cycle refreshes the addressed row.

2. Using a $\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle. If $\overline{CAS}$ makes a transition from low to high to low after the previous cycle and before $\overline{RAS}$ falls, $\overline{CAS}$-before-$\overline{RAS}$ refresh is activated. The V53C256A will use the output of an internal 8-bit counter as the source of row addresses and ignore external address inputs.

$\overline{CAS}$-before-$\overline{RAS}$ is a "refresh-only" mode and no data access or device selection is allowed. Thus, D_{OUT} will remain in the High-Z state during the cycle.

A $\overline{CAS}$-before-$\overline{RAS}$ counter test mode is provided to ensure reliable operation of the internal refresh counter. The user can use the counter test mode to write consecutive data patterns (256 write cycles) and then verify the written data by applying 256 consecutive read cycles. In this mode, the V53C256A ignores external row/column addresses and takes the output from the internal counter instead.

Data Retention Mode

The V53C256A offers a CMOS standby mode that is entered by causing the $\overline{RAS}$ clock to swing between a valid V_{IL} and an "extra high" V_{IH} within 0.2 V of V_{DD}. While the $\overline{RAS}$ clock is at the "extra high" level, the V53C256A power consumption is reduced to the low I_{DD6} level. Overall I_{DD} consumption when operating in this mode can be calculated as follows:

$$I = \frac{(t_{RC}) \times (I_{DD1}) + (t_{RX} - t_{RC}) \times (I_{DD6})}{t_{RX}}$$

Where t_{RC} = Refresh Cycle Time
t_{RX} = Refresh Interval / 256

Fast Page Mode Operation

Fast Page Mode operation permits all 512 columns within a selected row of the device to be randomly accessed at a high data rate. Maintaining $\overline{RAS}$ low while performing successive $\overline{CAS}$ cycles retains the row address internally and eliminates the need to reapply it for each cycle. The column address buffer acts as a transparent or flow-through latch while $\overline{CAS}$ is high.

Thus, access begins at the occurance of a valid column address rather than at the falling edge of $\overline{CAS}$, eliminating t_{ASC} and t_T from the critical timing path. $\overline{CAS}$ latches the address into the column address buffer and acts as on output enable.

During Fast Page Mode operation, Read, Write, Read-Modify-Write, or Read-Write-Read cycles are possible at random addresses within a row. Following the initial entry cycle into Fast Page Mode, access is t_{CAA} or t_{CAP} controlled. If the column address is valid prior to the rising edge of $\overline{CAS}$, the access time is determined by the by the $\overline{CAS}$ rising edge. If the column address is valid after the rising edge of $\overline{CAS}$, the access is timed from the occurrance of the valid address and is specified by t_{CAA}. In both cases, the falling edge of $\overline{CAS}$ latches the address and enables the output.

Fast Page Mode provides a sustained data rate of over 19 MHz for applications that require high data rates like bit-mapped graphics or high-speed signal processing. The following equation can be used to calculate the data rate:

$$\text{Data Rate} = \frac{512}{t_{RC} + 511 \times t_{PC}}$$

Data Output Operation

The V53C256A Data Output pin (D_{OUT}) has a three-state capability and is controlled by $\overline{CAS}$. When $\overline{CAS}$ is high($\geq V_{IH}$), the output is in the High-Z state. Table 1 summarizes the D_{OUT} states possible for various memory cycles.

Power-On

After application of the V_{DD} an initial pause of 200 µs is required followed by a minimum of 8 initialization cycles (any combination of cycles containing a $\overline{RAS}$ clock). Eight initialization cycles are required after extended periods of bias without clocks (greater than the Refresh Interval). During Power-On, the V_{DD} current requirement of the V53C256A is dependent on the input levels of $\overline{RAS}$ and $\overline{CAS}$. If $\overline{RAS}$ is low during power on, the device will go into an active cycle and I_{DD} will exhibit current transients. It is recommended that $\overline{RAS}$ and $\overline{CAS}$ track with V_{DD} or be held at a valid V_{IH} during Power-On to avoid current surges.

Table 1. Vitelic V53C256A Data Output
Operation for Various Cycle Types

Cycle Type	D_{OUT} State
Read Cycles	Data from Addressed Memory Cell
$\overline{CAS}$-Controlled Write Cycle (Early Write)	High-Z
$\overline{WE}$-Controlled Write Cycle (Late Write)	Active, not valid
Read-Modify-Write Cycles	Data from Addressed Memory Cell
Fast Page Mode Read Cycle	Data from Addressed Memory Cell
Fast Page Mode Write Cycle (Early Write)	High-Z
Fast Page Mode Read-Modify-Write Cycle	Data from Addressed Memory Cell
$\overline{RAS}$-only Refresh	High-Z
$\overline{CAS}$-before-$\overline{RAS}$ Refresh Cycle	Data remains as in previous cycle
$\overline{CAS}$-only Cycles	High-Z